Abstracts

Modeling of Transverse Propagation Delays in the GaAs/AlGaAs Modulation Doped Heterojunction Field Effect Transistors

A.K. Goel and W. Xu. "Modeling of Transverse Propagation Delays in the GaAs/AlGaAs Modulation Doped Heterojunction Field Effect Transistors." 1993 Transactions on Microwave Theory and Techniques 41.6 (Jun./Jul. 1993 [T-MTT]): 1230-1232.

We have developed a computer-efficient algorithm to calculate the transverse propagation delays in a GaAs/AlGaAs MODFET. The model includes the intrinsic as well as the extrinsic parameters of the MODFET. The dependence of these delays on the various MODFET parameters such as its gate length, width and the gate metal resistivity have been studied.

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